

# MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



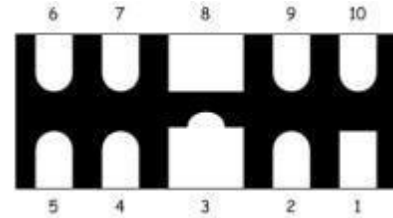
PLED

Product data sheet

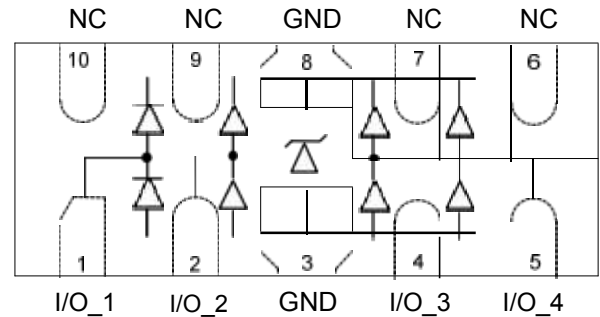
## Features

- Ultra low leakage: nA level
- Operating voltage: 5.0V
- Low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test  
Air discharge:  $\pm 30\text{kV}$   
Contact discharge:  $\pm 25\text{kV}$
  - IEC61000-4-4 (EFT) 40A (5/50ns)
  - IEC61000-4-5 (EFT) 5A (8/20ns)
- RoHS Compliant

## Dimensions DFN2510P10



## Pin Configuration



## Applications

- USB 2.0 power and data line
- Set-top box and digital TV
- Digital video interface (DVI)
- Notebook Computers
- SIM Ports
- 10/100 Ethernet

## Mechanical Characteristics

- Package: DFN2510P10
- Lead Finish: Lead Free
- UL Flammability Classification Rating 94V-0
- Quantity Per Reel: 3,000 pcs
- Reel Size: 7 inch

## Absolute Maximum Ratings (T<sub>amb</sub>=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 $\mu$ s)	P <sub>pp</sub>	150	W
ESD per IEC 61000-4-2 (Air)	V <sub>ESD</sub>	$\pm 15$	Kv
ESD per IEC 61000-4-2 (Contact)		$\pm 8$	
Operating Temperature Range	T <sub>J</sub>	-55 to +125	°C
Storage Temperature Range	T <sub>STJ</sub>	-55 to +150	°C

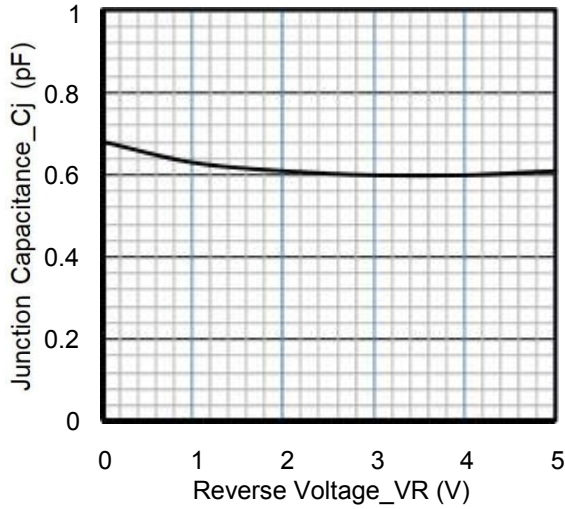
**Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	150	W
Peak Pulse Current (8/20μs)	I <sub>PP</sub>	5	A
ESD per IEC 61000-4-2 (Air)	V <sub>ESD</sub>	±30	kV
ESD per IEC 61000-4-2 (Contact)		±25	
Operating Temperature Range	T <sub>J</sub>	-55 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

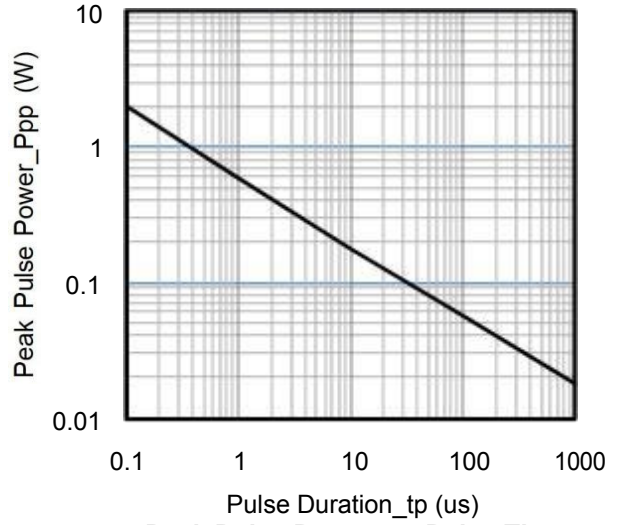
**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V <sub>RWM</sub>			5	V	Any I/O pin to ground
Breakdown Voltage	V <sub>BR</sub>	6			V	I <sub>T</sub> = 1mA, any I/O pin to ground
Reverse Leakage Current	I <sub>R</sub>			0.5	μA	V <sub>RWM</sub> = 5V, any I/O pin to ground
Clamping Voltage	V <sub>C</sub>			15	V	I <sub>PP</sub> = 1A (8 x 20μs pulse), any I/O pin to ground
Clamping Voltage	V <sub>C</sub>			20	V	I <sub>PP</sub> = 5A (8 x 20μs pulse), any I/O pin to ground
Junction Capacitance	C <sub>J</sub>		0.3	0.4	pF	V <sub>R</sub> = 0V, f = 1MHz, between I/O pins
Junction Capacitance	C <sub>J</sub>			0.8	pF	V <sub>R</sub> = 0V, f = 1MHz, any I/O pin to ground

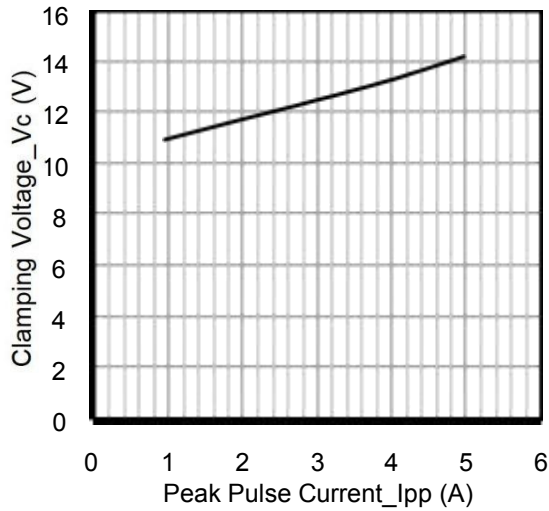
**Typical Performance Characteristics (T<sub>A</sub>=25°C unless otherwise Specified)**



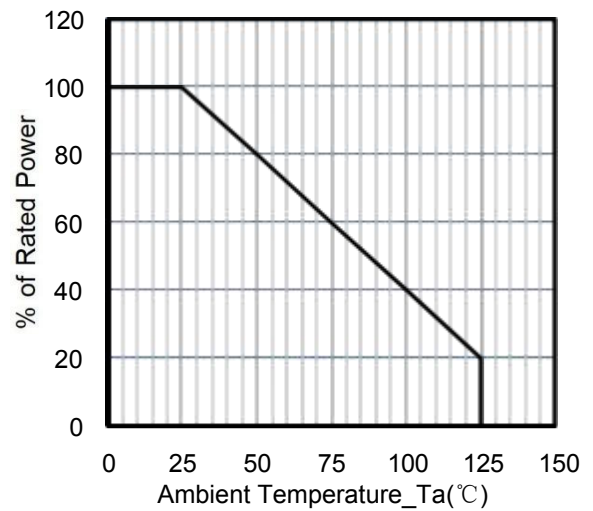
**Junction Capacitance vs. Reverse Voltage**



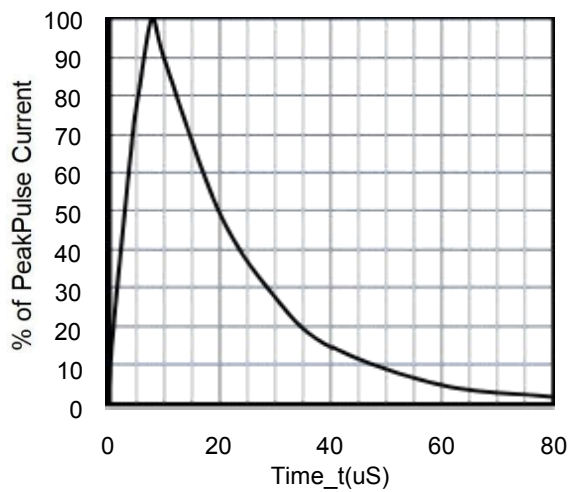
**Peak Pulse Power vs. Pulse Time**



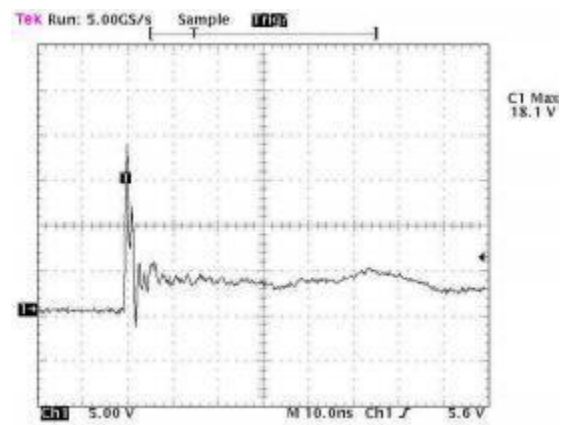
**Clamping Voltage vs. Peak Pulse Current**



**Power Derating Curve**



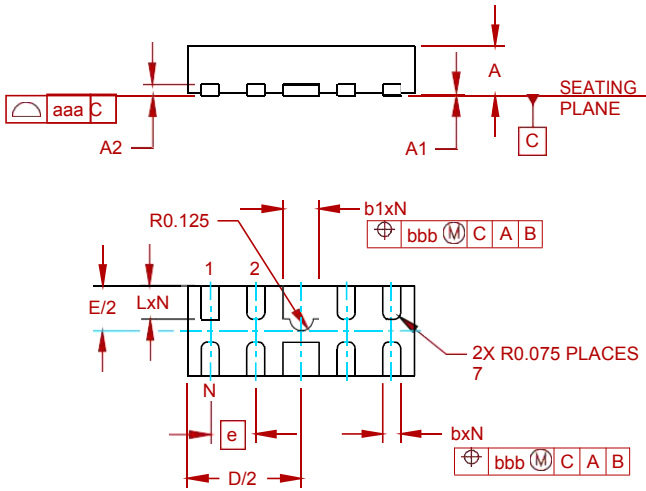
**8 X 20uS Pulse Waveform**



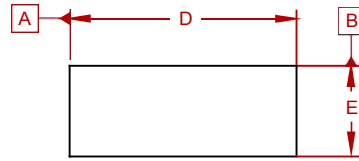
**ESD Clamping Voltage**

**8 kV Contact per IEC61000-4-2**

**PACKAGE MECHANICAL DATA**

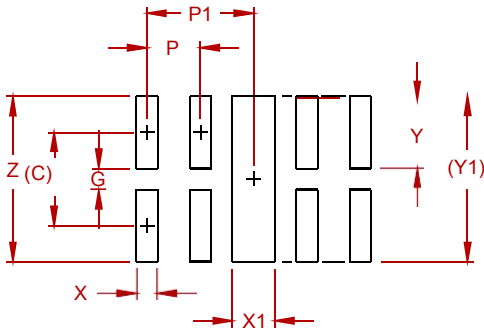


Dimensions in millimeters



DIM	DIMENSI ONS					
	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	.020	.023	.026	0.50	0.58	0.65
A1	0.00	.001	.002	0.00	0.03	0.05
A2	(.005)			(0.13)		
b	.006	.008	.010	0.15	0.20	0.25
b1	.014	.016	.018	0.35	0.40	0.45
D	.094	.098	.102	2.40	2.50	2.60
E	.035	.039	.043	0.90	1.00	1.10
e	.020 BSC			0.50 BSC		
L	.012	.015	.017	0.30	0.38	0.425
N	8			8		
aaa	.003			0.08		
bbb	.004			0.10		

**Suggested Pad Layout**



DIM	DIMENSIONS	
	INCHES	MILLIMETERS
C	(.034)	(0.875)
G	.008	0.20
P	.020	0.50
P1	.039	1.00
X	.008	0.20
X1	.016	0.40
Y	.027	0.675
Y1	(.061)	(1.55)
Z	.061	1.55

**NOTES:**

CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).  
THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY.  
CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

**REEL SPECIFICATION**

P/N	PKG	QTY
ULC0544P10-MS	DFN2510P10	3000

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